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Medium Power Phase Control Thyristors (Stud Version), 50 A



PRODUCT SUMMARY				
Package	TO-208AC (TO-65)			
Diode variation	Single SCR			
I _{T(AV)}	50 A			
V _{DRM} /V _{RRM}	100 V to 1200 V			
V _{TM}	1.60 V			
I _{GT}	100 mA			
T _J	-40 °C to 125 °C			

FEATURES

- High current rating
- Excellent dynamic characteristics
- dV/dt = 1000 V/µs option
- Superior surge capabilities
- Standard package
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- · Phase control applications in converters
- · Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		50	Α		
I _{T(AV)}	T _C	94	°C		
I _{T(RMS)}		80	Α		
I _{TSM}	50 Hz	1430	۸		
	60 Hz	1490	Α		
I ² t	50 Hz	10.18	kA ² s		
1-1	60 Hz	9.30	KA-S		
V _{DRM} /V _{RRM}		100 to 1200	V		
tq	Typical	110	μs		
TJ		-40 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ T_J &= T_J & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150				
	20	200	300				
	40	400	500				
VS-50RIA	60	600	700	15			
	80	800	900				
	100	1000	1100				
	120	1200	1300				

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $[\]ensuremath{^{(2)}}$ For voltage pulses with $t_p \leq 5 \ ms$



PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I	180° sinusoidal conduction		50	Α	
at case temperature	I _{T(AV)}	100 3110301	160 Sinusoidal conduction		94	°C
Maximum RMS on-state current	I _{T(RMS)}				80	Α
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		1490	_
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		1200	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1255	
Maximum I ² t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	10.18	kA ² s
	l ² t	t = 8.3 ms	reapplied		9.30	
		t = 10 ms	100 % V _{BBM}		7.20	
		t = 8.3 ms	reapplied		6.56	
Maximum $I^2\sqrt{t}$ for fusing	I ² √t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		101.8	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)}), T _J = T _J maximum		0.94	V	
High level value of threshold voltage	V _{T(TO)2}	$(\pi \times I_{T(AV)} < I$	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.08	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		4.08	mΩ	
High level value of on-state slope resistance	r _{t2}	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ 3.34		11152		
Maximum on-state voltage	V_{TM}	I _{pk} = 157 A, T _J = 25 °C		1.60	V	
Maximum holding current	I _H	T_J = 25 °C, anode supply 22 V, resistive load, initial I_T = 2 A		200	mA	
Latching current	ΙL	Anode supply 6 V, resistive load 400				

SWITCHING						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum rate of	$V_{DRM} \le 600 \text{ V}$	dl/dt	T_C = 125 °C, V_{DM} = Rated V_{DRM} , Gate pulse = 20 V, 15 Ω, t_p = 6 μs, t_r = 0.1 μs maximum		A/µs	
rise of turned-on current	$V_{DRM} \le 1600 \text{ V}$		$I_{TM} = (2 \text{ x rated dl/dt}) \text{ A}$	100	-/ μ5	
Typical delay time		t _d	$t_{\rm d}$ $T_{\rm C}$ = 25 °C, $V_{\rm DM}$ = Rated $V_{\rm DRM}$, $I_{\rm TM}$ = 10 A dc resistive circuit Gate pulse = 10 V, 15 Ω source, $t_{\rm p}$ = 20 μs			
Typical turn-off time		tq	$t_{\rm q}$ $T_{\rm C}$ = 125 °C, $I_{\rm TM}$ = 50 A, reapplied dV/dt = 20 V/ μ s dIr/dt = -10 A/ μ s, $V_{\rm R}$ = 50 V		μs	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of	d\//dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	200	\//uo	
off-state voltage	dV/dt	T _J = T _J maximum linear to 67 % rated V _{DRM}	500 ⁽¹⁾	V/µs	

Note

 $^{^{(1)}}$ Available with dV/dt = 1000 V/ μs , to complete code add S90 i.e. 50RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum, $t_p \le \xi$	$T_J = T_J$ maximum, $t_p \le 5$ ms		W
Maximum average gate power	P _{G(AV)}			2.5	, vv
Maximum peak positive gate current	I _{GM}			2.5	А
Maximum peak positive gate voltage	+V _{GM}			20	V
Maximum peak negative gate voltage	-V _{GM}			10	V
	I _{GT}	T _J = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V	250	mA
DC gate current required to trigger		T _J = 25 °C		100	
		T _J = 125 °C		50	
DC gate valte as veguined to trigger	V	T _J = - 40 °C	anode to cathode applied	3.5	V
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5	1 V
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated voltage	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to 0.2 cathode applied		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.35	K/W	
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased	0.25	r\/ VV	
Allowable requesting toward		Non-lubricated threads	3.4 + 0 - 10 % (30)	N · m	
Allowable mounting torque		Lubricated threads	2.3 + 0 - 10 % (20)	(lbf·in)	
Approximate weight			28	g	
Approximate weight			1.0	OZ.	
Case style		See dimensions - link at the end of datasheet TO-208AC ((TO-65)	

△R _{th} JC CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.078	0.057					
120°	0.094	0.098					
90°	0.120	0.130	$T_J = T_J \text{ maximum}$	K/W			
60°	0.176	0.183					
30°	0.294	0.296					

Note

The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

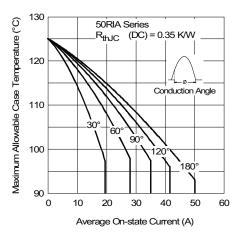


Fig. 1 - Current Ratings Characteristics

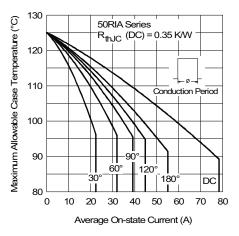


Fig. 2 - Current Ratings Characteristics

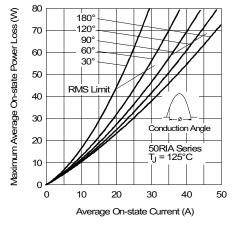


Fig. 3 - On-State Power Loss Characteristics

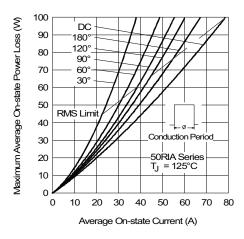


Fig. 4 - On-State Power Loss Characteristics

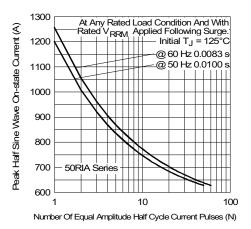


Fig. 5 - Maximum Non-Repetitive Surge Current

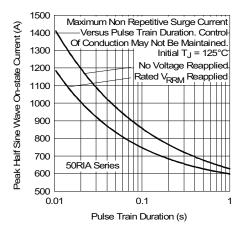


Fig. 6 - Maximum Non-Repetitive Surge Current

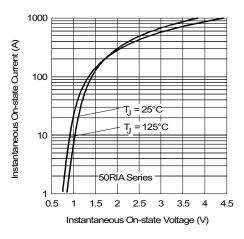


Fig. 7 - Forward Voltage Drop Characteristics

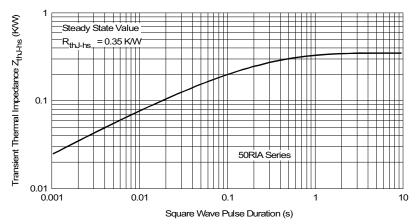


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

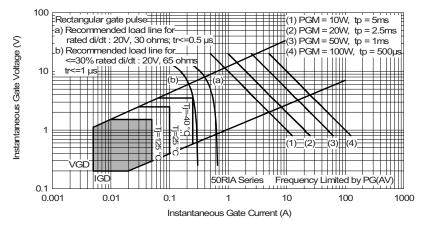
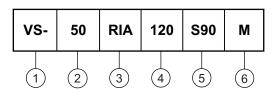


Fig. 9 - Gate Characteristics



ORDERING INFORMATION TABLE

Device code



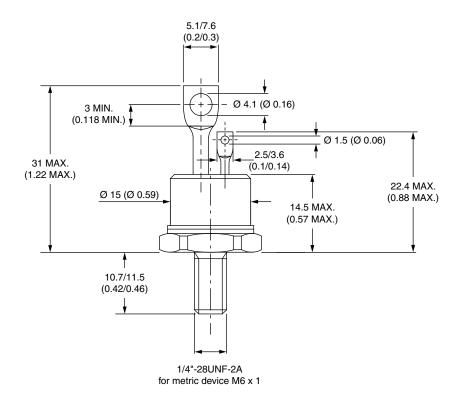
- Vishay Semiconductors product
- 2 Current code
- Essential part number
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 5 Critical dV/dt:
 - None = 500 V/µs (standard value)
 - S90 = 1000 V/µs (special selection)
- 6 • None = Stud base TO-208AC (TO-65) 1/4" 28UNF-2A
 - M = Stud base TO-208AC (TO-65) M6 x 1

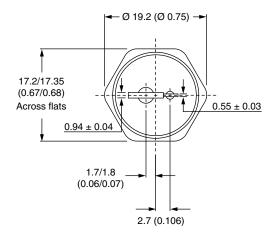
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95334		



TO-208AC (TO-65)

DIMENSIONS in millimeters (inches)







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